What is claimed is:

1. An electric device comprising:

a substrate;

an active matrix circuit including at least one thin film transistor;

driving means including at least another one thin film transistor for driving the active matrix circuit; and

at least one semiconductor integrated circuit chip for controlling the driving means,

wherein the active matrix circuit, the driving means and semiconductor integrated circuit chip are formed on the substrate.

2. The device of claim 1 wherein the semiconductor integrated circuit chip is connected with the driving means by a wire bonding.

3. The device of claim 1 wherein the semiconductor integrated circuit chip is connected with the driving means by a COG (chip on glass).

4. The device of claim 1 wherein the semiconductor integrated circuit chip has a central processing unit.

5. The device of claim 1 wherein the semiconductor integrated circuit chip has a memory.

6. The device of claim 1 wherein the substrate has glass.

7. A liquid crystal display device comprising:

a substrate having a glass;

an active matrix circuit including at least one thin film transistor;

driving means including at least another one thin film transistor for driving the active matrix circuit; and

control means for controlling the driving means,

wherein the active matrix circuit, the driving means and the control means are formed on the substrate.

8. The device of claim 7 wherein the control means has at least one semiconductor integrated circuit chip.

9. The device of claim 8 wherein the semiconductor integrated circuit chip has a central processing unit.

10. The device of claim 8 wherein the semiconductor integrated circuit chip has a memory.

11. A liquid crystal display device comprising:

a substrate;

an active matrix circuit including at least one thin film transistor;

driving means including at least another one thin film transistor for driving the active matrix circuit; and

control means for controlling the driving means, the control means being connected with the driving means by a COG (chip on glass),

wherein the active matrix circuit, the driving means and the control means are formed on the substrate.

12. The device of claim 11 wherein the substrate has glass.

13. The device of claim 11 wherein the control means has at least one semiconductor integrated circuit chip.

14. A liquid crystal display device comprising:

a substrate;

an active matrix circuit including at least one thin film transistor;

driving means including at least another one thin film transistor for driving the active matrix circuit; and

control means for controlling the driving means, the control means being connected with the driving means by a wire bonding,

wherein the active matrix circuit, the driving means and the control means are formed on the substrate.

15. The device of claim 14 wherein the substrate has glass.

16. The device of claim 14 wherein the control means has at least one semiconductor integrated circuit chip.

17. An electric device comprising:

a substrate;

a plurality of thin film transistors formed on the

substrate; and

at least one semiconductor integrated circuit chip formed on the substrate,

wherein at least one of the thin film transistors is provided as an active matrix circuit, at least another one of the thin film transistors is provided as at least one driving circuit for driving the active matrix circuit, and the semiconductor integrated circuit chip is provided as a control circuit for controlling the driving circuit.

18. The device of claim 17 wherein the substrate has glass.

19. The device of claim 17 wherein the semiconductor integrated circuit chip is connected with the driving circuit by a wire bonding.

20. The device of claim 17 wherein the semiconductor integrated circuit chip is connected with the driving circuit by a COG (chip on glass).

21. An electric device comprising:

a pair of substrates opposite to each other;

an active matrix circuit;

a driving circuit for driving the active matrix circuit; and

a semiconductor integrated circuit chip,

wherein the active matrix circuit, the driving circuit and the semiconductor integrated circuit are formed on one of the substrate, and

wherein the driving circuit has at least an X-decoder/driver and a Y-decoder/driver and is formed by at least one thin film transistor.

22. The device of claim 21 wherein the thin film transistor is a complementary type.

23. The device of claim 21 wherein the thin film transistor has only P-type TFT.

24. The device of claim 21 wherein the thin film transistor has only N-type TFT.

25. An electric device comprising:

at least one thin film transistor forming an active matrix circuit; and

at least another one thin film transistor having the substantially same structure as that of the one thin film transistor,

wherein the structure includes the same material as at least one of a gate electrode material, a gate insulating material and a channel forming material in the one thin film transistor.